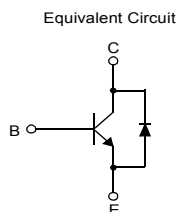
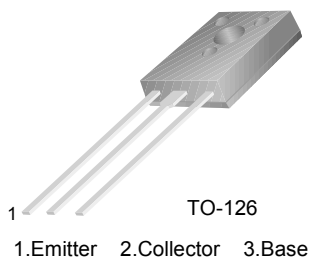


# FJE5304D

## NPN Triple Diffused Planar Silicon Transistor

### High Voltage High Speed Power Switch Application

- Wide Safe Operating Area
- Built-in Free Wheeling diode
- Suitable for Electronic Ballast Application
- Small Variance in Storage Time



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	700	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	12	V
I <sub>C</sub>	Collector Current (DC)	4	A
I <sub>CP</sub>	* Collector Current (Pulse)	8	A
I <sub>B</sub>	Base Current (DC)	2	A
I <sub>BP</sub>	* Base Current (Pulse)	4	A
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	30	W
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

\* Pulse Test Pulse Width = 5ms, Duty Cycle ≥ 1.0%

### Electrical Characteristics T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA, I <sub>E</sub> = 0	700			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0	400			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA, I <sub>C</sub> = 0	12			V
I <sub>CES</sub>	Collector Cut-off Current	V <sub>CE</sub> = 700V, V <sub>EB</sub> = 0			100	μA
I <sub>CEO</sub>	Collector Cut-off Current	V <sub>CE</sub> = 400V, I <sub>B</sub> = 0			250	μA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 12V, I <sub>C</sub> = 0			100	μA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA V <sub>CE</sub> = 5V, I <sub>C</sub> = 2A	10 8		40	

**Electrical Characteristics** (Continued)  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$ $I_C = 1\text{A}, I_B = 0.2\text{A}$ $I_C = 2.5\text{A}, I_B = 0.5\text{A}$			0.7 1.0 1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 0.5\text{A}, I_B = 0.1\text{A}$ $I_C = 1\text{A}, I_B = 0.2\text{A}$ $I_C = 2.5\text{A}, I_B = 0.5\text{A}$			1.1 1.2 1.3	V
$V_f$	Internal Diode Forward Voltage Drop	$I_F = 2\text{A}$			2.5	V
<b>Inductive Load Switching (<math>V_{CC} = 200\text{V}</math>)</b>						
$t_{stg}$	Storage Time	$I_C = 2\text{A}, I_{B1} = 0.4\text{A}$ $V_{BE(off)} = -5\text{V}$ $L = 200\mu\text{H}$		0.6		$\mu\text{s}$
$t_f$	Fall Time			0.1		
<b>Resistive Load Switching (<math>V_{CC} = 250\text{V}</math>)</b>						
$t_{stg}$	Storage Time	$I_C = 2\text{A}, I_{B1} = I_{B2} = 0.4\text{A}$ $T_P = 30\mu\text{s}$			2.9	$\mu\text{s}$
$t_f$	Fall Time			0.2		

\* Pulse test:  $PW \leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$

**Thermal Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted

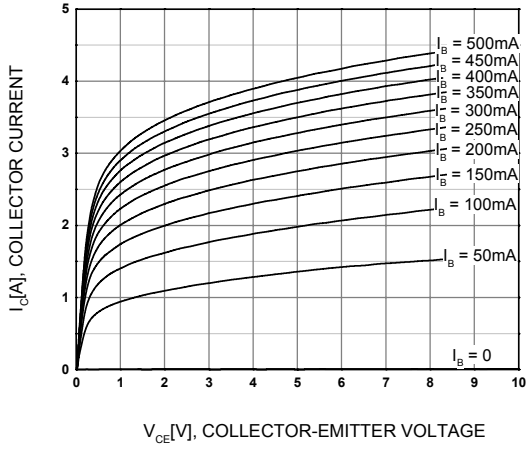
Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.17	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	83.3	$^\circ\text{C/W}$

**Package Marking and Ordering Information**

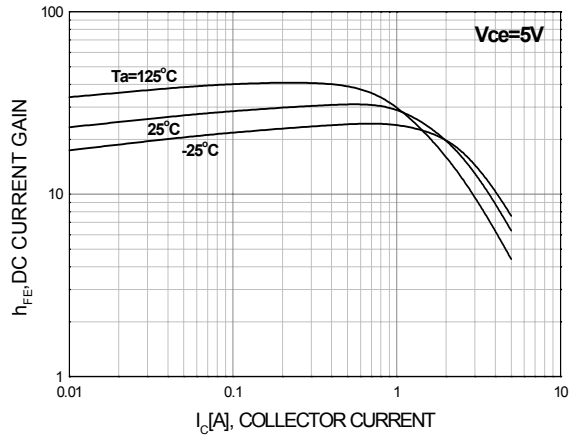
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FJE5304D	FJE5304D	TO-126	--	--	--

## Typical Performance Characteristics

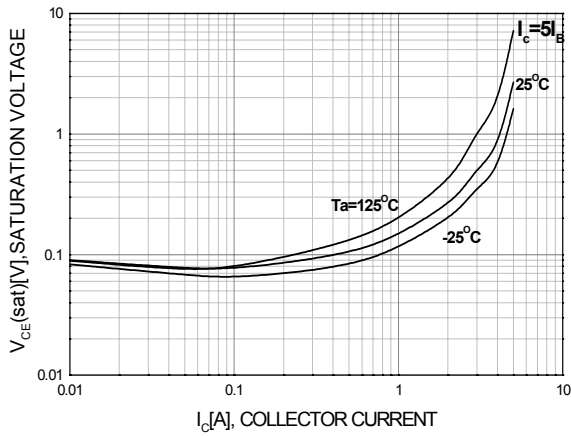
**Figure 1. Static Characteristic**



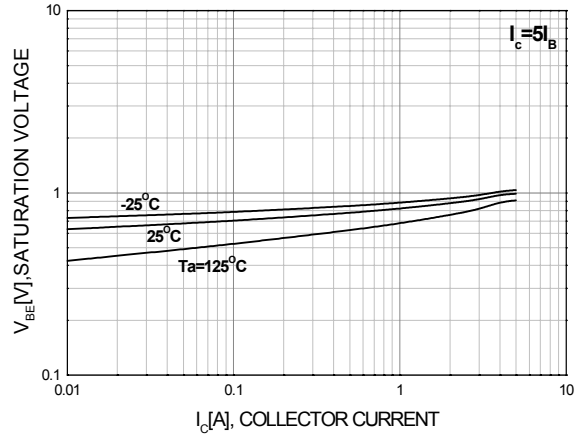
**Figure 2. DC Current Gain**



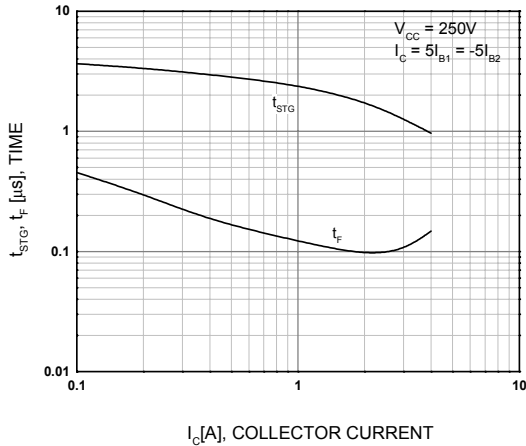
**Figure 3. Collector-Emitter Saturation Voltage**



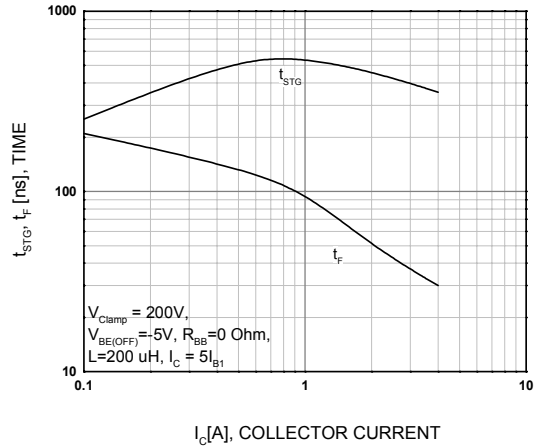
**Figure 4. Base-Emitter Saturation Voltage**



**Figure 5. Resistive Load Switching Time**

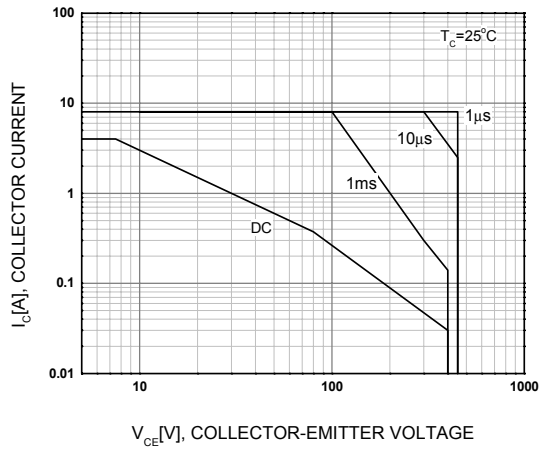


**Figure 6. Inductive Load Switching Time**

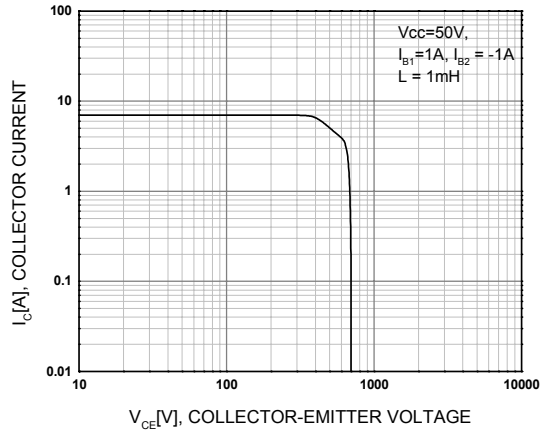


## Typical Performance Characteristics

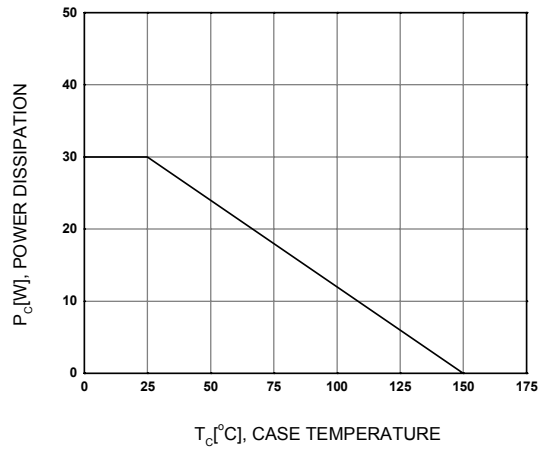
**Figure 7. Forward Bias Safe Operating Area**



**Figure 8. Reverse Bias Safe Operating Area**

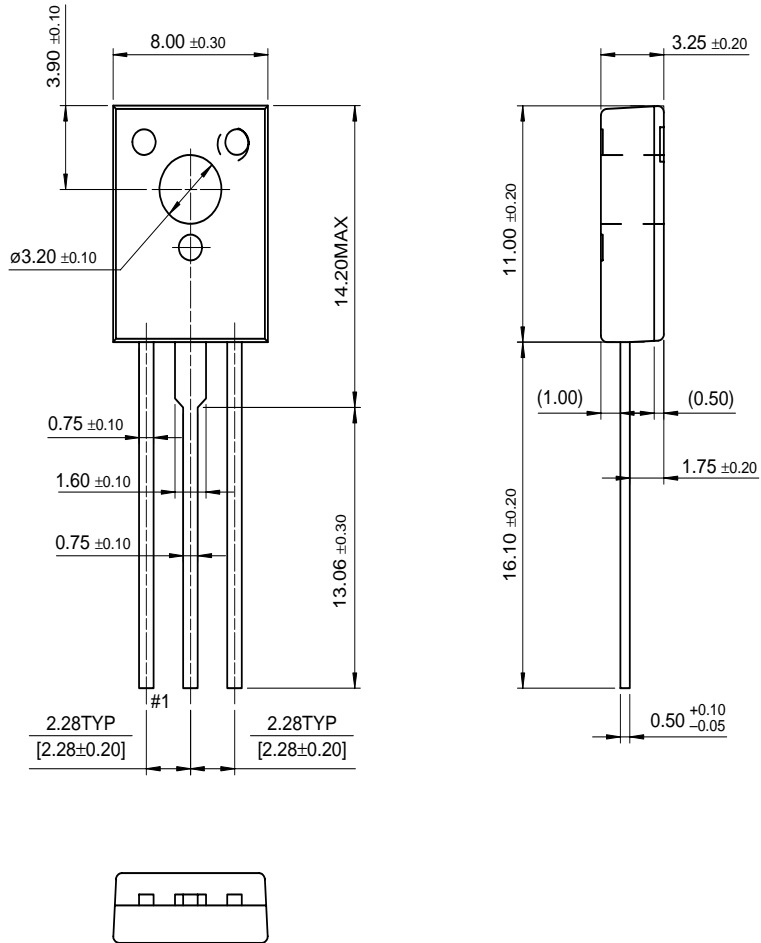


**Figure 9. Power Derating**



**Mechanical Dimensions**

**TO-126**



Dimensions in Millimeters

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EcoSPARK™	I <sup>2</sup> C™	MSXPro™	RapidConnect™	UniFET™
E <sup>2</sup> CMOS™	i-Lo™	OCX™	μSerDes™	VCX™
EnSigna™	ImpliedDisconnect™	OCXPro™	SILENT SWITCHER®	Wire™
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		PowerEdge™	SuperSOT™-6	

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